

NPN POWER TRANSISTOR SILICON AMPLIFIER

Qualified per MIL-PRF-19500/583

Devices

2N5681

2N5682

Qualified Level

JAN
JANTX
JANTXV

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

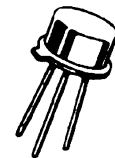
Ratings	Symbol	2N5681	2N5682	Units
Collector-Emitter Voltage	V_{CEO}	100	120	Vdc
Collector-Base Voltage	V_{CBO}	100	120	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	4.0	Vdc
Collector Current	I_C	1.0	1.0	Adc
Base Current	I_B	0.5	0.5	Adc
Total Power Dissipation	P_T	@ $T_A = +25^\circ\text{C}^{(1)}$	1.0	W
		@ $T_C = +25^\circ\text{C}^{(2)}$	10	W
Operating & Storage Temperature Range	T_{op}, T_{stg}	-65 to +200	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	17.5	$^\circ\text{C}$

1) Derate linearly 5.7 mW/ $^\circ\text{C}$ for $T_A > +25^\circ\text{C}$

2) Derate linearly 57 mW/ $^\circ\text{C}$ for $T_C > +25^\circ\text{C}$



TO-39*
(TO-205AD)

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	100 120		Vdc
Emitter-Base Cutoff Current $V_{EB} = 4.0 \text{ Vdc}$	I_{EBO}		1.0	μAdc
Collector-Emitter Cutoff Current $V_{CE} = 70 \text{ Vdc}$ $V_{CE} = 80 \text{ Vdc}$	I_{CEO}		10	μAdc
Collector-Emitter Cutoff Current $V_{BE} = 1.5 \text{ Vdc}$ $V_{CE} = 100 \text{ Vdc}$ $V_{CE} = 120 \text{ Vdc}$	I_{CEX}		100	nAdc
Collector-Base Cutoff Current $V_{CE} = 100 \text{ Vdc}$ $V_{CE} = 120 \text{ Vdc}$	I_{CBO}		100	nAdc

2N5681, 2N5682 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽³⁾				
Forward Current Transfer Ratio I _C = 250 mA _{dc} , V _{CE} = 2.0 V _{dc} I _C = 500 mA _{dc} , V _{CE} = 2.0 V _{dc} I _C = 1.0 A _{dc} , V _{CE} = 2.0 V _{dc}	h _{FE}	40 20 5	150	
Collector-Emitter Saturation Voltage I _C = 250 mA _{dc} , I _B = 25 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{CE(sat)}		0.6 1.0	V _{dc}
Base-Emitter Saturation Voltage I _C = 250 mA _{dc} , I _B = 25 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{BE(sat)}		1.1 1.3	V _{dc}

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short Circuit Forward-Current Transfer Ratio I _C = 0.1 A _{dc} , V _{CE} = 10 V _{dc} , f = 10 kHz	h _{fe}	3.0		
Small Signal Short Circuit Forward-Current Transfer Ratio I _C = 0.2 A _{dc} , V _{CE} = 1.5 V _{dc} , f = 1.0 kHz	h _{fe}	40		
Output Capacitance V _{CB} = 20 V _{dc} , I _E = 0, f = 1 MHz	C _{obo}		50	pF

SAFE OPERATING AREA

<p>DC Tests T_C = +25°C, 1 Cycle, t ≥ 0.5 s</p> <p>Test 1 V_{CE} = 2 V_{dc}, I_C = 1.0 A_{dc}</p> <p>Test 2 V_{CE} = 10 V_{dc}, I_C = 1.0 A_{dc}</p> <p>Test 3 V_{CE} = 90 V_{dc}, I_C = 50 mA_{dc}</p>
